

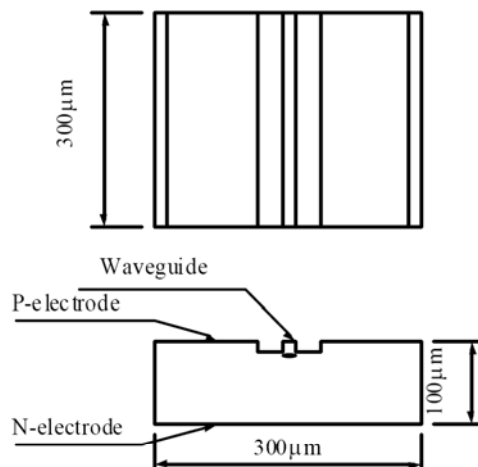


CHIP-980-P50

■ Specifications

- (1) Size : 300*300*100 μm
- (2) Device: Laser diode bare chip
- (3) Structure Double channel , single ridge waveguide

■ External dimensions(Unit : μm)



P-electrode and N-electrode are both gold pad.

Channel depth : 1 ~ 1.5 μm

■ Absolute Maximum Ratings($T_c=25^\circ\text{C}$)

Parameter	Symbol	Rating	Unit
Optical Output	Po	50	mW
Reverse Voltage	Vr	2	V
Operating Temperature	Top	-10 ~ +40	°C
Storage Temperature	Tstg	-15 ~ +85	°C



■ Electrical and Optical Characteristics (T_c=25°C)

Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
Threshold Current		I _{th}	-	-	12	20	mA
Operating Current		I _{op}	P _o =50mW	-	75	85	mA
Operating Voltage		V _{op}	-	1	1.5	2.1	Volt
Slope Efficiency		η	30mW-10mW	0.65	0.8	-	mW/mA
			I _{30mW} -I _{10mW}				
Beam Divergence (FWHM)	Parallel	$\theta //$	P _o =50mW	8	13	18	deg.
	Perpendicular	$\theta \perp$	P _o =50mW	25	30	35	deg.
Lasing Wavelength		λ	P _o =50mW	970	980	995	nm

© $\theta //$ and $\theta \perp$ are defined as the angle within which the intensity is 50% of the peak value.

© Measuring Conditions : Pulse width=5 μ s , Duty cycle=1%

SPECIFICATIONS ARE SUBJECT TO CHANGE WITHOUT NOTICE.